

L Number	Hits	Search Text	DB	Time stamp
1	10	(tunnel near4 diode) same (edge near3 emitt\$4 near3 laser)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 14:46
2	9	((tunnel near4 diode) same (edge near3 emitt\$4 near3 laser)) and reverse	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 13:56
3	3	(tunnel with diode with reverse with bias\$4) and (edge near3 emitt\$4 near3 laser)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 14:47
4	6	((tunnel with diode) same (reverse with bias\$4)) and (edge near3 emitt\$4 near3 laser)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 14:04
5	3	((tunnel with diode) same (reverse with bias\$4)) and (edge near3 emitt\$4 near3 laser) not ((tunnel with diode with reverse with bias\$4) and (edge near3 emitt\$4 near3 laser))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 14:46
6	2752	(372/43,46).CCLS.	USPAT; US-PGPUB	2004/03/04 14:46
7	276	((372/43,46).CCLS.) and (edge near3 emitt\$4 near3 laser)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 14:46
8	5	((372/43,46).CCLS.) and (tunnel with diode with reverse with bias\$4)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 14:47
9	2	((372/43,46).CCLS.) and (edge near3 emitt\$4 near3 laser)) and ((372/43,46).CCLS.) and (tunnel with diode with reverse with bias\$4))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 14:47
-	1	6515313.pn. and c with axis	USPAT; EPO; JPO; IBM_TDB	2003/06/24 14:58
-	3	(semiconductor near3 laser) and (c with axis with reverse)	USPAT; EPO; JPO; IBM_TDB	2003/11/23 19:35
-	1587	(semiconductor near3 laser) and (c with axis) or ("0001" with orientation)	USPAT; EPO; JPO; IBM_TDB	2003/06/24 15:00
-	1435	(semiconductor near3 laser) and ((c with axis) or ("0001" with orientation))	USPAT; EPO; JPO; IBM_TDB	2003/06/24 15:00
-	98	((semiconductor near3 laser) and ((c with axis) or ("0001" with orientation))) and GaN	USPAT; EPO; JPO; IBM_TDB	2003/06/24 15:00
-	29	((semiconductor near3 laser) and ((c with axis) or ("0001" with orientation))) and wurtzite	USPAT; EPO; JPO; IBM_TDB	2003/06/24 15:00
-	26	((semiconductor near3 laser) and ((c with axis) or ("0001" with orientation))) and GaN) and (((semiconductor near3 laser) and ((c with axis) or ("0001" with orientation))) and wurtzite)	USPAT; EPO; JPO; IBM_TDB	2003/06/24 15:01
-	7	((semiconductor near3 laser) and ((c with axis) or ("0001" with orientation))) and GaN) and (((semiconductor near3 laser) and ((c with axis) or ("0001" with orientation))) and wurtzite)) and reverse	USPAT; EPO; JPO; IBM_TDB	2003/06/24 15:01
-	0	6515313.pn. and (tilt\$3 angl\$4) with (substrate base layer)	USPAT; EPO; JPO; IBM_TDB	2003/06/24 15:31

-	0	6515313.pn. and (tilt\$3 angl\$4)	USPAT; EPO; JPO; IBM_TDB	2003/06/24 15:36
-	1	6294440.pn.	USPAT; EPO; JPO; IBM_TDB	2003/06/24 15:37
-	1	6294440.pn. and reverse	USPAT; EPO; JPO; IBM_TDB	2003/06/24 15:37
-	29	(semiconductor near3 laser) and (reverse\$3 with bias\$3) same ( tunnel with junction)	USPAT; EPO; JPO; IBM_TDB	2003/11/23 18:33
-	27	((semiconductor near3 laser) and (reverse\$3 with bias\$3) same ( tunnel with junction)) and active	USPAT; EPO; JPO; IBM_TDB	2003/11/23 18:33
-	13	(semiconductor near4 laser) and (c with axis with revers\$4)	USPAT; EPO; JPO; IBM_TDB	2003/11/23 19:41
-	269	wurtzite and laser	USPAT; EPO; JPO; IBM_TDB	2003/11/23 19:41
-	15	wurtzite with axis and semiconductor near3 laser	USPAT; EPO; JPO; IBM_TDB	2003/11/23 19:43
-	0	wurtzite same axis same revers\$3 same c	USPAT; EPO; JPO; IBM_TDB	2003/11/23 19:43
-	0	wurtzite same axis same revers\$3	USPAT; EPO; JPO; IBM_TDB	2003/11/23 19:43
-	60	wurtzite same axis same c	USPAT; EPO; JPO; IBM_TDB	2003/11/23 19:44
-	43	wurtzite with axis with c	USPAT; EPO; JPO; IBM_TDB	2003/11/23 19:44
-	2	(wurtzite with axis with c) and c with revers\$4	USPAT; EPO; JPO; IBM_TDB	2003/11/23 19:52
-	14	(wurtzite with axis with c) and semiconductor near3 laser	USPAT; EPO; JPO; IBM_TDB	2003/11/23 19:45
-	1	(revers\$4 with c with axis) same (semiconductor near3 laser)	USPAT; EPO; JPO; IBM_TDB	2003/11/23 19:54
-	0	revers\$4 same "c-axis" same nitrogen same (semiconductor near3 laser)	USPAT; EPO; JPO; IBM_TDB	2003/11/23 19:54
-	0	revers\$4 same "c-axis" same (semiconductor near3 laser)	USPAT; EPO; JPO; IBM_TDB	2003/11/23 19:56
-	106	revers\$4 same "c-axis"	USPAT; EPO; JPO; IBM_TDB	2003/11/23 19:54
-	19	(revers\$4 same "c-axis" ) and ("N" nitrogen) with (face side surface)	USPAT; EPO; JPO; IBM_TDB	2003/11/23 19:55
-	65259	GaN same c-axis sme (semiconductor near3 laser)	USPAT; EPO; JPO; IBM_TDB	2003/11/23 19:56
-	5	GaN same c-axis same (semiconductor near3 laser)	USPAT; EPO; JPO; IBM_TDB	2003/11/23 20:03

-	120	((planar flat) with substrate) and ((tilt\$4 angl\$4) with active) and (semiconductor near3 laser)	USPAT; EPO; JPO; IBM_TDB	2003/11/23 20:04
-	10	((((planar flat) with substrate) and ((tilt\$4 angl\$4) with active) and (semiconductor near3 laser)) and junction) and polarization	USPAT; EPO; JPO; IBM_TDB	2003/11/23 20:04
-	2	("5418374"   "6414976").PN.	USPAT	2003/11/23 20:06
-	68	((planar flat) with substrate) and ((tilt\$4 angl\$4) with active) and (semiconductor near3 laser)) and junction	USPAT; EPO; JPO; IBM_TDB	2003/11/23 20:21
-	1	5814531.URPN.	USPAT	2003/11/23 20:08
-	8	("4404678"   "4569721"   "4946802"   "5149670"   "5202285"   "5255281"   "5336635"   "5375136").PN.	USPAT	2003/11/23 20:08
-	8	("4404678"   "4569721"   "4946802"   "5149670"   "5202285"   "5255281"   "5336635"   "5375136").PN.	USPAT	2003/11/23 20:13
-	52	((planar flat) with substrate) and ((tilt\$4 angl\$4) with active) and (semiconductor near3 laser)) not (((planar flat) with substrate) and ((tilt\$4 angl\$4) with active) and (semiconductor near3 laser)) and junction)	USPAT; EPO; JPO; IBM_TDB	2003/11/23 20:23
-	172	372/43-50.ccls. and (tilt\$3 angl\$4) near5 active	USPAT; EPO; JPO; IBM_TDB	2003/11/23 20:25
-	143	(372/43-50.ccls. and (tilt\$3 angl\$4) near5 active) not (((planar flat) with substrate) and ((tilt\$4 angl\$4) with active) and (semiconductor near3 laser))	USPAT; EPO; JPO; IBM_TDB	2003/11/23 20:24
-	9	372/43-50.ccls. and (tilt\$3 near5 active)	USPAT; EPO; JPO; IBM_TDB	2003/11/23 20:25
-	1	5693965.URPN.	USPAT	2003/11/23 20:27
-	3	("3888388"   "4520485"   "5602864").PN.	USPAT	2003/11/23 20:27